

# 2SD1458

## Silicon NPN epitaxial planar type

For low-frequency amplification

### ■ Features

- High forward current transfer ratio  $h_{FE}$
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	20	V
Collector-emitter voltage (Base open)	$V_{CEO}$	20	V
Emitter-base voltage (Collector open)	$V_{EBO}$	15	V
Collector current	$I_C$	0.7	A
Peak collector current	$I_{CP}$	1.5	A
Collector power dissipation *	$P_C$	1	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

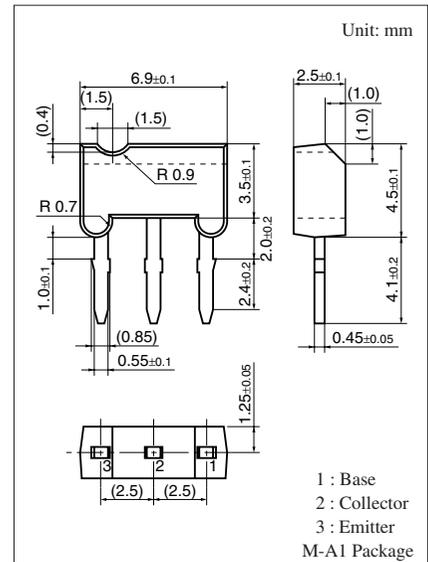
Note) \*: Printed circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion

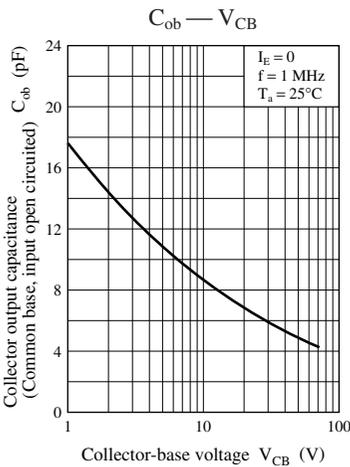
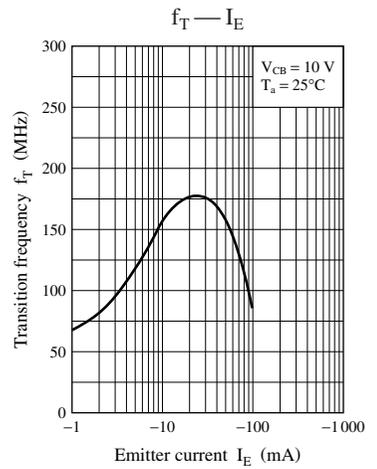
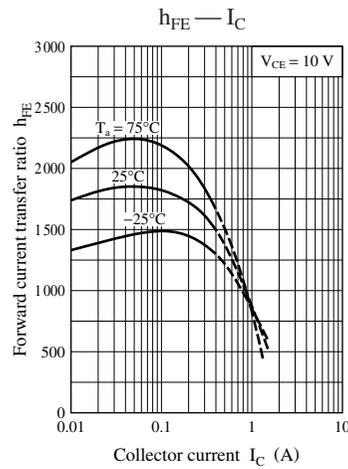
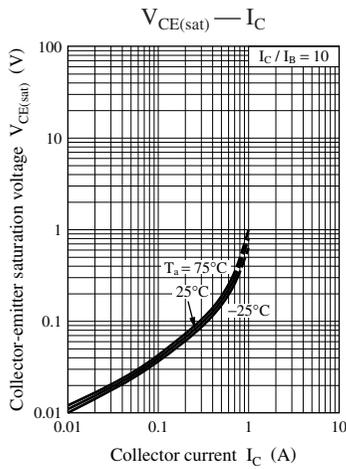
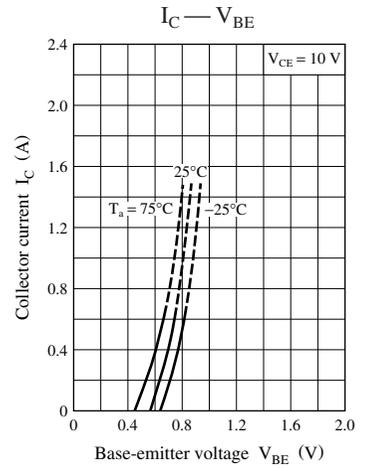
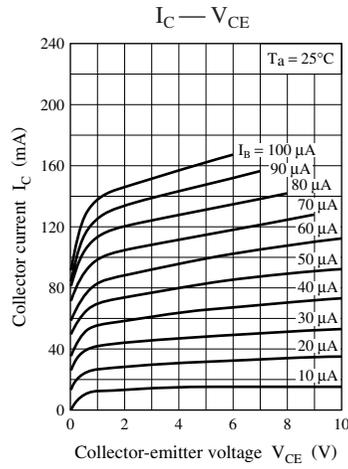
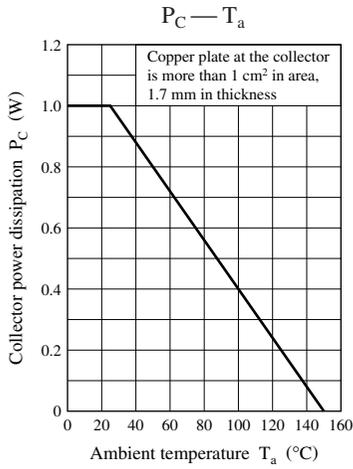
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}$ , $I_E = 0$	20			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 1 \text{ mA}$ , $I_B = 0$	20			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}$ , $I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 15 \text{ V}$ , $I_E = 0$			1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 15 \text{ V}$ , $I_B = 0$			10	$\mu\text{A}$
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = 10 \text{ V}$ , $I_C = 150 \text{ mA}$	1000		2500	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 \text{ mA}$ , $I_B = 50 \text{ mA}$			0.4	V
Transition frequency	$f_T$	$V_{CB} = 20 \text{ V}$ , $I_E = -20 \text{ mA}$ , $f = 200 \text{ MHz}$		55		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = 10 \text{ V}$ , $I_E = 0$ , $f = 1 \text{ MHz}$		11	15	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Pulse measurement





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